Vishay Semiconductors

Ultrafast Rectifier, 2 x 8 A FRED Pt[®]



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PRODUCT SUMMARY					
Package	TO-263AC (SMPD)				
I _{F(AV)}	2 x 8 A				
V _R	600 V				
V _F at I _F	0.94 V				
t _{rr}	45 ns				
T _J max.	175 °C				
Diode variation	Dual die				

FEATURES

- Ultrafast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- For PFC CRM, snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop, ultrafast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in PFC, boost, in the AC/DC section of SMPS, freewheeling and clamp diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage		V _{RRM}		600	V		
Average rectified forward current	per device		T _{solder pad} = 149 °C	16			
	per diode	IF(AV)		8			
	per device	I	$T_J = 25 \text{ °C}, 6 \text{ ms square pulse}$	200	A		
Non-repetitive peak surge current	per diode	IFSM		105			

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-		
Ferward valtage ner diade	V _F	I _F = 8 A	-	1.1	1.4	V	
Forward voltage, per diode		I _F = 8 A, T _J = 150 °C	-	0.94	1.15		
Deverse leekees surrent per diede		$V_{R} = V_{R}$ rated	-	-	5		
Reverse leakage current, per diode	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	20	150	μA	
Junction capacitance, per diode	CT	V _R = 600 V	-	8	-	pF	

Revision: 10-Feb-15 1 Document Number: 95814 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>





FREE



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}$	õs, V _R = 30 V	-	45	-	
Reverse recovery time	+	$I_{\rm F} = 0.5 \; {\rm A}, I_{\rm R} = 1 \; {\rm A}, I_{\rm rr}$	-	-	60		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	70	-	ns .
		T _J = 125 °C		-	100	-	
Deck receiver a surrent		T _J = 25 °C	$I_{\rm F} = 8 {\rm A},$	-	12	-	^
Peak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = 500 A/µs, V _R = 400 V	-	17	-	A
D	Q _{rr}	T _J = 25 °C]	-	430	-	
Reverse recovery charge		T _J = 125 °C		-	850	-	nC

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	+175	°C	
Thermal resistance, per diode junction to solder pad	R _{thJ-Sp}		-	1.8	2.5	°C/W	
Approximate weight				0.55		g	
Approximate weight				0.02		oz.	
Marking device		Case style TO-263AC (SMPD)		16CI	DU06		

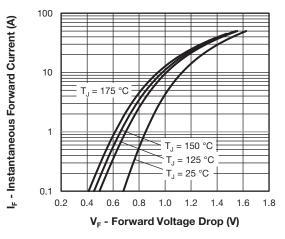
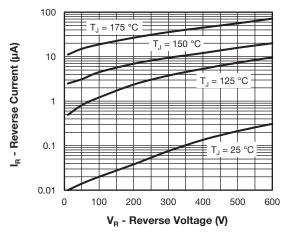
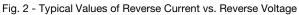


Fig. 1 - Typical Forward Voltage Drop Characteristics





VS-16CDU06-M3

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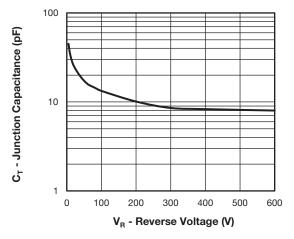


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

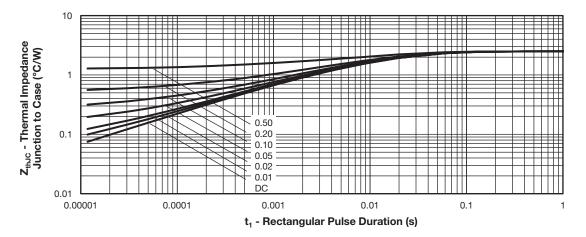
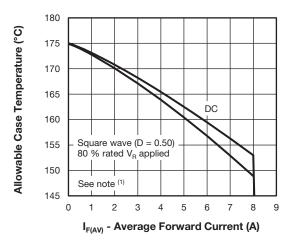
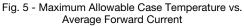


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics





Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ x \ \mathsf{V}_{\mathsf{FM}} \ at \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see fig. 5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ x \ \mathsf{I}_{\mathsf{R}} \ (1 - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ at \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

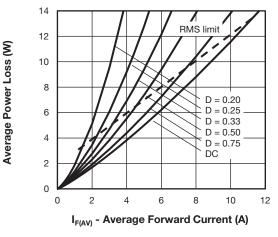


Fig. 6 - Forward Power Loss Characteristics

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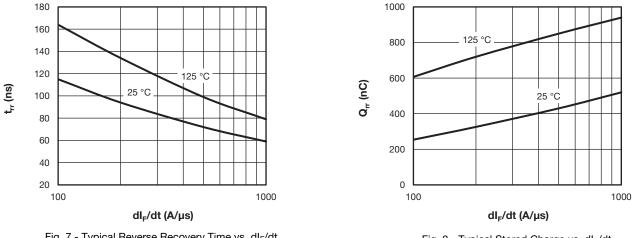
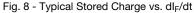


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

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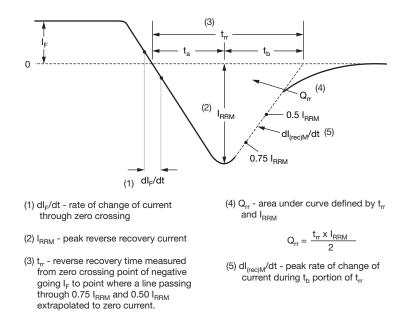


Fig. 9 - Reverse Recovery Waveform and Definitions

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Device code	VS-	16	С	D	U	06	-M3
	1	2	3	4	5	6	7
	1	- Visł	nay Sem	nicondu	ctors pr	oduct	
	2	- Cur	rent rati	ng (16 A	A)		
	3	- Circ	cuit cont	figuratio	n:		
		C =	commo	on catho	de		
	4	- D=	SMPD	packag	е		
	5	- Pro	cess typ	be,			
		U =	ultrafas	t recove	ery		
	6	- Volt	age coo	de (06 =	600 V)		
	7	M3	3 = halog	gen-free	e, RoHS	-compl	iant, and

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-16CDU06-M3/I	2000	2000	13" diameter plastic tape and reel					

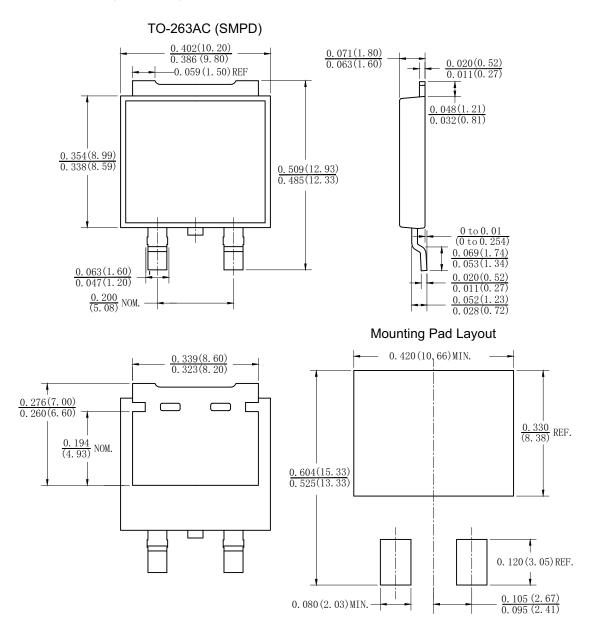
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95604				
Part marking information	www.vishay.com/doc?95566				
Packaging information	www.vishay.com/doc?88869				





TO-263AC (SMPD)

DIMENSIONS in inches (millimeters)





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